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20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = 25°C
20V	18.5mΩ @ V _{GS} = 10V	5.4 A
	$21m\Omega$ @ $V_{GS} = 4.5V$	5.0 A
	$24m\Omega$ @ $V_{GS} = 2.5V$	4.6 A
	31mΩ @ V _{GS} = 1.8V	3.5 A

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

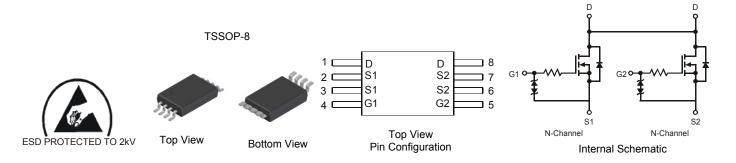
- Power management functions
- Load Switch

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected up to 2KV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

- Case: TSSOP-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.039 grams (approximate)



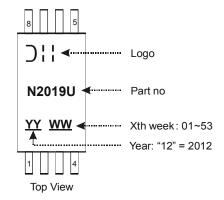
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2019UTS-13	TSSOP-8	2500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	5.4 4.3	А
Continuous Drain Current (Note 5) V _{GS} = 2.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	4.6 3.7	А
Continuous Body Diode Forward Current (Note 5) Steady Stat T _A = +25°C			Is	0.9	А
Pulsed Drain Current (Note 5) 10µs pulse, duty cyc	I _{DM}	30	Α		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_{D}	0.78	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	161	°C/W
Thermal Resistance, Junction to Case (Note 5)	$R_{ heta JC}$	26	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

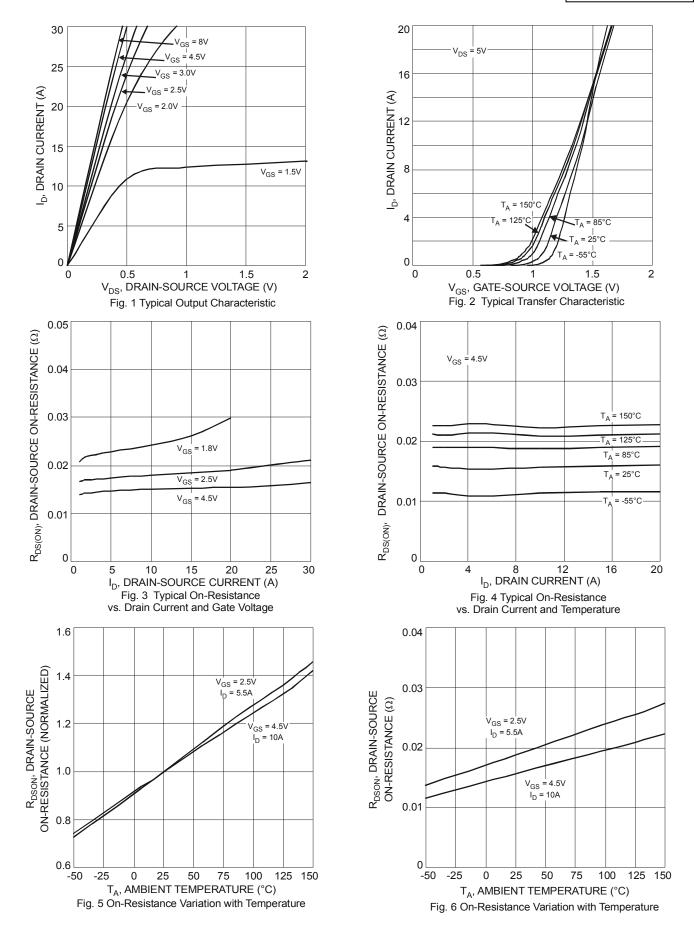
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage		20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current		-	-	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	10	μA	$V_{GS} = \pm 10V$, $V_{DS} = 0V$	
Gate-Source Breakdown Voltage	BV _{SGS}	±12	-	-	V	$V_{DS} = 0V$, $I_{G} = \pm 250 \mu A$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(th)}	0.35	-	0.95	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			15.5	18.5		$V_{GS} = 10V, I_D = 7A$	
		-	16.5	21		$V_{GS} = 4.5V, I_D = 7A$	
		-	17	21.5		$V_{GS} = 4.0V, I_D = 7A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	-	17.5	22.5	mΩ	$V_{GS} = 3.6V, I_D = 6.5A$	
		-	18	23		$V_{GS} = 3.1V, I_D = 6.5A$	
		-	19	24		$V_{GS} = 2.5V, I_D = 5.5A$	
			24	31		$V_{GS} = 1.8V, I_D = 3.5A$	
Forward Transfer Admittance	Y _{fs}	1	13	-	S	$V_{DS} = 5V$, $I_D = 5A$	
Diode Forward Voltage	V_{SD}	-	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	-	143	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	74	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	29	-	pF		
Gate Resistance	R_{g}	ı	202	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	1	8.8	-	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 6.5A	
Gate-Source Charge	Q_{gs}	-	1.4	-	nC		
Gate-Drain Charge	Q_{gd}	-	3.0	-	nC		
Turn-On Delay Time	t _{D(on)}	-	53	-	ns	V _{DD} = 10V, V _{GS} = 4.5V,	
Turn-On Rise Time	t _r	-	78	-	ns		
Turn-Off Delay Time	t _{D(off)}	-	562	-	ns	$R_L = 10\Omega$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _f	-	234	-	ns	1	

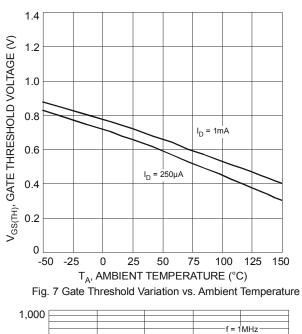
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

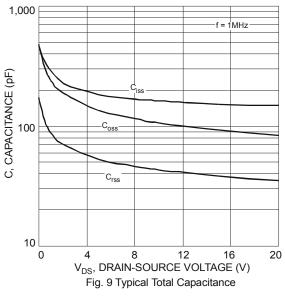
Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

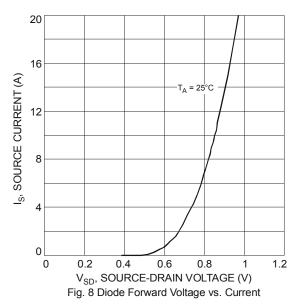


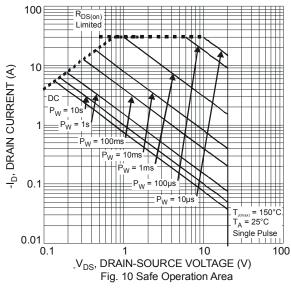












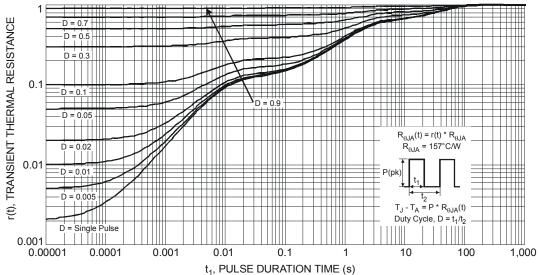
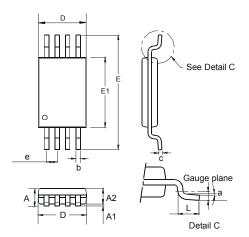


Fig. 11 Transient Thermal Response



Package Outline Dimensions

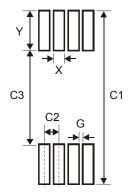
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



TSSOP-8					
Dim	Min	Max	Тур		
а	0.09	_	-		
Α	_	1.20	_		
A1	0.05	0.15	-		
A2	0.825	1.025	0.925		
b	0.19	0.30	-		
С	0.09	0.20	_		
D	2.90	3.10	3.025		
е	-	-	0.65		
E	_	_	6.40		
E1	4.30	4.50	4.425		
Ĺ	0.45	0.75	0.60		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Х	0.45		
Υ	1.78		
C1	7.72		
C2	0.65		
C3	4.16		
G	0.20		



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